

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2SK1875

HIGH FREQUENCY AMPLIFIER APPLICATIONS

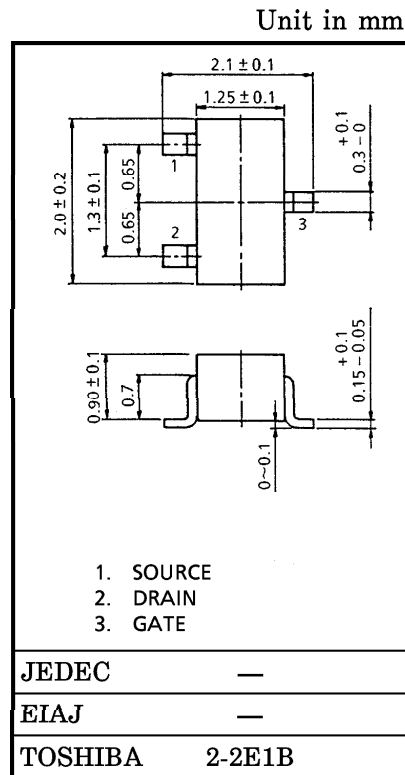
AM HIGH FREQUENCY AMPLIFIER APPLICATIONS

AUDIO FREQUENCY AMPLIFIER APPLICATIONS

- High $|Y_{fs}|$: $|Y_{fs}| = 25\text{mS}$ (Typ.)
- Low C_{iss} : $C_{iss} = 7.5\text{pF}$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V _{GD} S	-20	V
Gate Current	I _G	10	mA
Drain Power Dissipation	P _D	100	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



Weight : 0.006 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

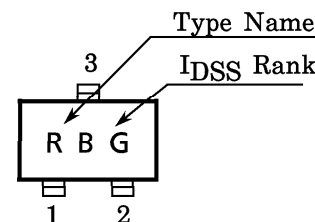
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I _{GSS}	V _{GS} = -15V, V _{DS} = 0V	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	V _(BR) GDS	V _{DS} = 0V, I _G = -100μA	-20	—	—	V
Drain Current	I _{DSS} (Note)	V _{DS} = 5V, V _{GS} = 0V	6	—	32	mA
Gate-Source Cut-off Voltage	V _{GS} (OFF)	V _{DS} = 5V, I _D = 1μA	—	—	-2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 5V, V _{GS} = 0V, f = 1kHz	15	25	—	mS
Input Capacitance	C _{iss}	V _{DS} = 5V, V _{GS} = 0V, f = 1MHz	—	7.5	10	pF
Reverse Transfer Capacitance	C _{rss}	V _{DG} = 5V, I _D = 0V, f = 1MHz	—	2	3	pF

Note : I_{DSS} Classification

GR : 6~12mA, BL : 10~20mA, V : 16~32mA
(G) (L) (V)

()...I_{DSS} Rank Marking

Marking



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